

is extended to the next business day.

In the Claims:

Amend claims 1 and 53 as follows:

C1 sub 07  
1. (Amended) A method comprising the step of annealing at least one region of a semiconductor substrate while minimizing the diffusion of dopant atoms during activation by using a pulsed beam of particles having a time duration less than or equal to  $10^{-4}$  seconds.

C2  
53. (Amended) A method comprising the steps of annealing at least one integrated device formed in a semiconductor substrate while minimizing the diffusion of dopant atoms during activation by using a pulsed beam of particles having a duration between  $10^{-10}$  seconds and  $10^{-4}$  seconds.

REMARKS

Claims 1, 7, 14, 16-20, 22-23, 53, 61, 63-66, 69 and 71-72 were again rejected by the Examiner as being obvious from Asakawa (JP 06340500). Of those claims, claims 1 and 53 are independent claims and will be addressed first.

As amended, Claim 1 calls for "annealing at least one region of a semiconductor substrate **while minimizing the diffusion of dopant atoms during activation** by using a pulsed beam of particles having a time duration less than or equal to  $10^{-4}$  seconds".

As amended, Claim 53 calls for "annealing at least one integrated device formed in a semiconductor substrate **while minimizing the diffusion of dopant atoms during activation** by using a pulsed beam of particles having a duration between  $10^{-10}$  seconds and  $10^{-4}$  seconds".